

IN THE CLAIMS:

Please amend the application by canceling claims 1 and 16 without prejudice or disclaimer, and entering the amended claims as set forth below in marked-up form. In accordance with the revised amendment format now permitted, a clean copy of the claims has been omitted.

1. (Cancelled)

2. (Currently Amended) A solid-state imaging device as claimed in claim ~~1~~3, wherein said electrode and said light-shielding film have an oxide film interposed between them.

C' 3. (Currently Amended) ~~A solid-state imaging device as claimed in claim 1, wherein said first film is a tungsten film~~ A solid-state imaging device, which comprises:

a light-receiving portion formed on a semiconductor substrate; and

a light-shielding film formed so as to cover an electrode formed on said semiconductor substrate on regions of said semiconductor substrate other than a region above said light-receiving portion;

wherein said solid-state imaging device is formed such that said light-shielding film has a multilayer structure including a first film formed of a tungsten film deposited by sputtering or vapor deposition and a second film deposited by chemical vapor deposition.

4. (Currently Amended) ~~A solid state imaging device as claimed in claim 1, wherein said second film is a tungsten film~~ A solid-state imaging device, which comprises:

a light-receiving portion formed on a semiconductor substrate; and

a light-shielding film formed so as to cover an electrode formed on said semiconductor substrate on regions of said semiconductor substrate other than a region above said light-receiving portion;

wherein said solid-state imaging device is formed such that said light-shielding film has a multilayer structure including a first film formed of a film deposited by sputtering or vapor deposition and a second film formed of a tungsten film deposited by chemical vapor deposition.

5. (Currently Amended) A solid-state imaging device as claimed in claim 4, wherein said electrode is a transfer electrode.

6. (Currently Amended) A solid-state imaging device as claimed in claim 4, wherein said electrode is made of polysilicon.

Claims 7-16 (Cancelled)

17. (Currently Amended) ~~The solid state imaging device as set forth in claim 16,~~ A solid-state imaging device, comprising:

a semiconductor substrate;

a light-receiving portion formed on said substrate; and

a light-shielding film formed to cover an electrode formed on said semiconductor substrate on its regions other than a region above said light-receiving portion, said light-shielding film comprising a multilayer structure including a first film formed as an adhesion film and deposited by sputtering or vapor deposition, and a second film deposited by chemical vapor deposition;

wherein said first film is formed of a tungsten film and said second film is formed of a tungsten film.

C' 18. (Currently Amended) The solid-state imaging device as set forth in claim ~~16~~17, wherein said electrode is a transfer electrode formed on the semiconductor substrate at its area other ~~that~~ than the area in which the light-receiving portion is formed through a gate insulating film, said light-shielding film formed on the transfer electrode through an interlayer insulating film, said light-shielding film preventing light from becoming incident on the transfer electrode.

19. (Previously Presented) The solid-state imaging device as set forth in claim 18, further comprising an interlayer insulating film formed over the surface of the light-shielding film, a planarization film formed over the surface of the interlayer insulating film, a color filter formed on the planarization film, and a micro-lens formed on the color filter.

20. (Previously Presented) The solid-state imaging device as set forth in claim 17 wherein said first film of

tungsten has a thickness in a range of 20 to 100 nm, and said second film of tungsten has a thickness in a range of about 80 nm to 200 nm so as to maintain a satisfactory light-shielding property.

21. (Currently Amended) A solid state imaging device according to claim 13, wherein said first film has a thickness in a range of 20 to 100 nm, and said second film has a thickness in a range of about 80 nm to 200 nm so as to maintain a satisfactory light-shielding property.

C1 22. (Currently Amended) A solid-state imaging device according to claim 13, wherein the entirety of the light-shielding film is less than 200 nm.

23. (Currently Amended) A solid-state imaging device according to claim 14, wherein the entirety of the light-shielding film is less than 200 nm.

24. (Currently Amended) A solid-state imaging device according to claim 13, wherein the entirety of the light-shielding film is approximately 100 nm.

25. (Currently Amended) A solid-state imaging device according to claim 14, wherein the entirety of the light-shielding film is approximately 100 nm.

26. (New) A solid-state imaging device, comprising:
a light-receiving portion formed on a semiconductor substrate; and

a light-shielding film formed so as to cover an electrode formed on said semiconductor substrate on its region other than a region above said light-receiving portion;

C' wherein said light-shielding film has a multilayer structure including a first film formed of a first material capable of being deposited by sputtering or vapor deposition and a second film formed of a second material capable of being deposited by chemical vapor deposition.

27. (New) A solid-state imaging device according to claim 26, wherein both said first film and said second film are formed of tungsten.

28. (New) A solid-state imaging device according to claim 26, wherein said first film is formed of aluminum, gold, chromium, molybdenum silicide, or tungsten silicide.
